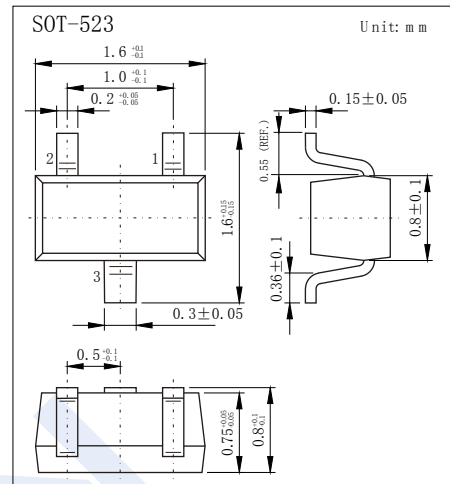
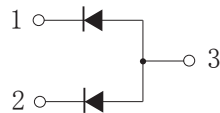


## Switching Diodes

## DAP222 (KAP222)

## ■ Features

- High speed
- Suitable for high packing density layout
- High reliability

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	$V_{RM}$	80	V
DC Reverse Voltage	$V_R$	80	
Average forward current	$I_o$	100	mA
Peak Forward Surge Current	$I_{FM}$	300	
Power Dissipation	$P_d$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100 \mu\text{A}$	80			V
Forward voltage	$V_F$	$I_F = 100\text{mA}$			1.2	
Reverse voltage leakage current	$I_R$	$V_R = 70 \text{V}$			0.1	$\mu\text{A}$
Junction capacitance	$C_j$	$V_R = 6 \text{V}, f = 1 \text{MHz}$			3.5	pF
Reverse recovery time	$t_{rr}$	$I_F = I_R = 5\text{mA}, V_R = 6\text{V}$			4	ns

## ■ Marking

Marking	P